



# SANYO SEMICONDUCTOR

## 2SC2271

2SC2271 — NPN Triple Diffused Planar Type Silicon Transistor  
For Picture Output or Driver of H-Deflection

### Absolute Maximum Ratings at Ta=25°C

Collector to Base Voltage	VCBO	300	V
Collector to Emitter Voltage	VCEO	300	V
Emitter to Base Voltage	VEBO	6	V
Collector Current	IC	100	mA
	icp	300	mA
Power Dissipation	PC	750	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

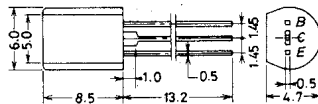
### Electrical Characteristics at Ta=25°C

		min	typ	max	unit
Collector Cut Off Current	ICBO V <sub>CB</sub> =200V, I <sub>E</sub> =0			1.0	uA
Emitter Cut Off Current	IEBO V <sub>EB</sub> =6V, I <sub>C</sub> =0			1.0	uA
DC Current Gain	h <sub>FE</sub> * V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	40*		200*	
Gain Band Width Product	f <sub>T</sub> V <sub>CE</sub> =30V, I <sub>C</sub> =10mA	50			MHz
Output Capacitance	cob V <sub>CB</sub> =10V, f=1MHz			7.5	pF
C-E Saturation Voltage	V <sub>CE(sat)</sub> I <sub>C</sub> =20mA, I <sub>B</sub> =2mA			0.6	V
B-E Saturation Voltage	V <sub>BE(sat)</sub>			1.0	V

h<sub>FE</sub>\* is classified as follows:

2SC2271 C:	40	80
2SC2271 D:	60	120
2SC2271 E:	100	200

### Case Outline(unit:mm)



EIAJ: SC-51  
SANYO: MP

B: Base  
C: Collector  
E: Emitter